



# STD40N2LH5 STU40N2LH5

N-channel 25 V, 0.01  $\Omega$ , 40 A, DPAK, IPAK  
STripFET™ V Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STD40N2LH5	25 V	0.0118 $\Omega$	40 A
STU40N2LH5	25 V	0.0124 $\Omega$	40 A

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses

## Application

- Switching applications

## Description

This STripFET™ V Power MOSFET technology is among the latest improvements, which have been especially tailored to achieve very low on-state resistance providing also one of the best-in-class figure of merit (FOM).

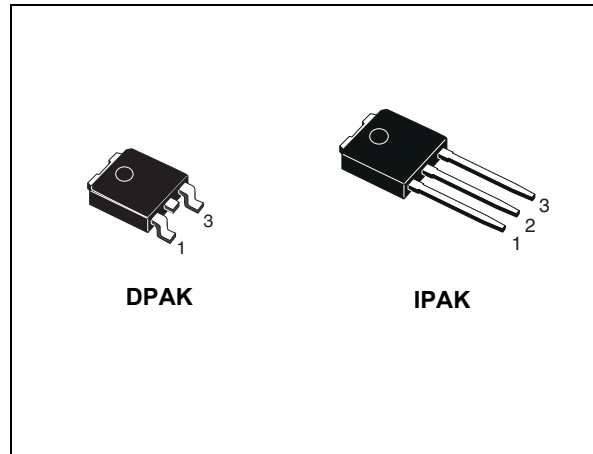


Figure 1. Internal schematic diagram

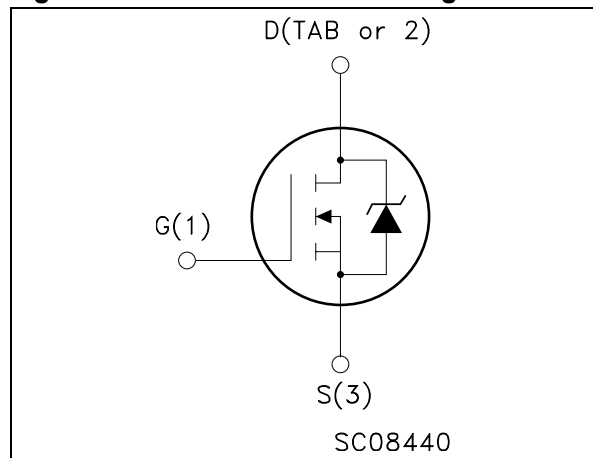


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD40N2LH5	40N2LH5	DPAK	Tape and reel
STU40N2LH5	40N2LH5	IPAK	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS}=0$ )	25	V
$V_{GS}$	Gate-Source voltage	$\pm 22$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	40	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	28	A
$I_{DM}^{(1)}$	Drain current (pulsed)	160	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	35	W
	Derating factor	0.23	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	110	mJ
$T_j$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 24\text{ A}$ ,  $V_{DD} = 12\text{ V}$

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	4.3	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-case max	100	$^\circ\text{C/W}$
$T_l$	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE} = 25^{\circ}C$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	25			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 25 V$ $V_{DS} = 25 V, T_C = 125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 22 V$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 20 A$ SMD version		0.01	0.0118	$\Omega$
		$V_{GS} = 10 V, I_D = 20 A$		0.0106	0.0124	$\Omega$
		$V_{GS} = 5 V, I_D = 20 A$ SMD version		0.0135	0.0155	$\Omega$
		$V_{GS} = 5 V, I_D = 20 A$		0.0141	0.0161	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 20 V, f = 1 MHz,$ $V_{GS} = 0$	-	700	-	pF
$C_{oss}$	Output capacitance			160		pF
$C_{rss}$	Reverse transfer capacitance			27		pF
$Q_g$	Total gate charge	$V_{DD} = 15 V, I_D = 40 A$	-	6.3	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 5 V$		2.4		nC
$Q_{gd}$	Gate-drain charge	( <i>Figure 14</i> )		2.7		nC

**Table 6. Switching on/off (resistive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time	$V_{DD} = 10 V, I_D = 20 A,$ $R_G = 4.7 \Omega, V_{GS} = 10 V$ ( <i>Figure 13</i> and <i>Figure 18</i> )	-	4.8	-	ns
	Rise time			13.6		
$t_{d(off)}$ $t_f$	Turn-off delay time	$V_{DD} = 10 V, I_D = 20 A,$ $R_G = 4.7 \Omega, V_{GS} = 10 V$ ( <i>Figure 13</i> and <i>Figure 18</i> )	-	17.6	-	ns
	Fall time			3.5		

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		40	A
$I_{SDM}$	Source-drain current (pulsed) <sup>(1)</sup>		-		160	A
$V_{SD}$	Forward on voltage	$I_{SD}= 20\text{ A}$ , $V_{GS}=0$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD}= 40\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}= 20\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$ ( <i>Figure 15</i> )	-	17.6		ns
$Q_{rr}$	Reverse recovery charge			9.2		nC
$I_{RRM}$	Reverse recovery current			1		A

1. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

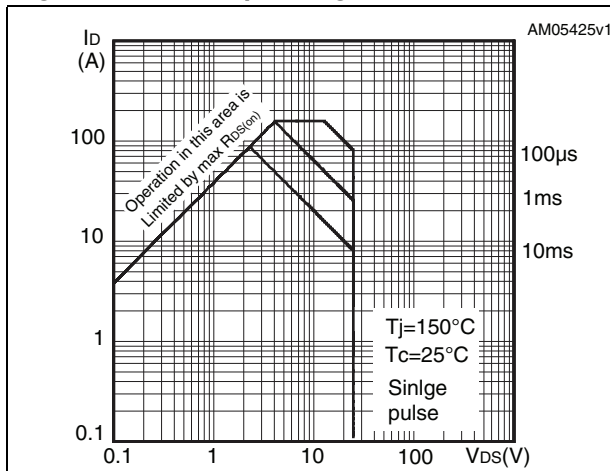


Figure 3. Thermal impedance

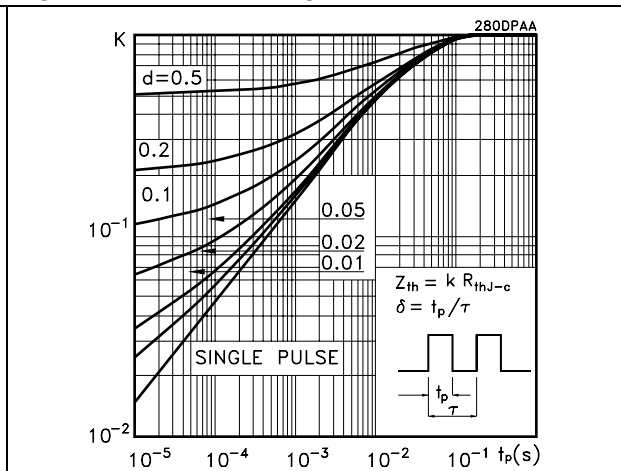


Figure 4. Output characteristics

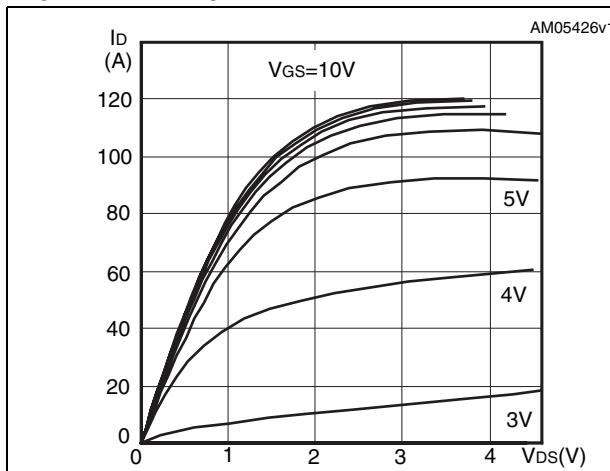


Figure 5. Transfer characteristics

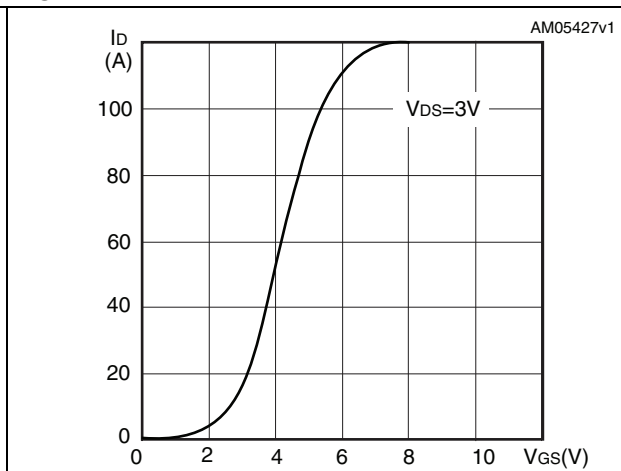


Figure 6. Normalized BV<sub>DSS</sub> vs temperature

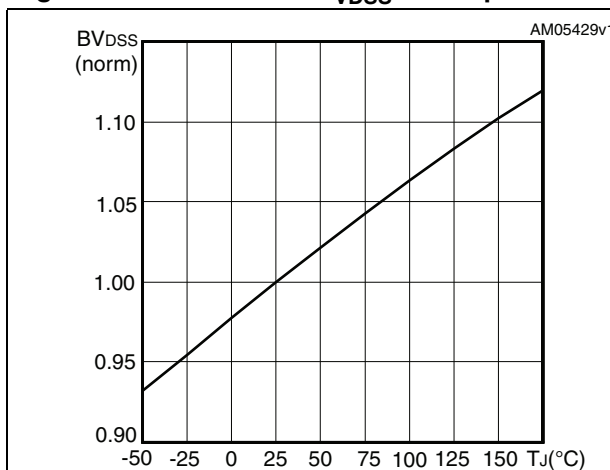


Figure 7. Static drain-source on resistance

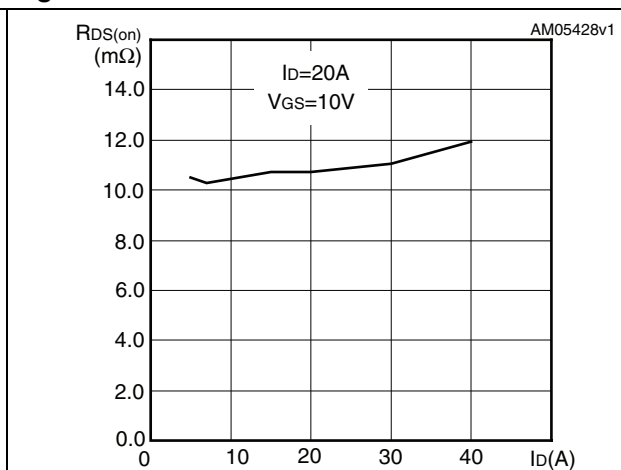


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

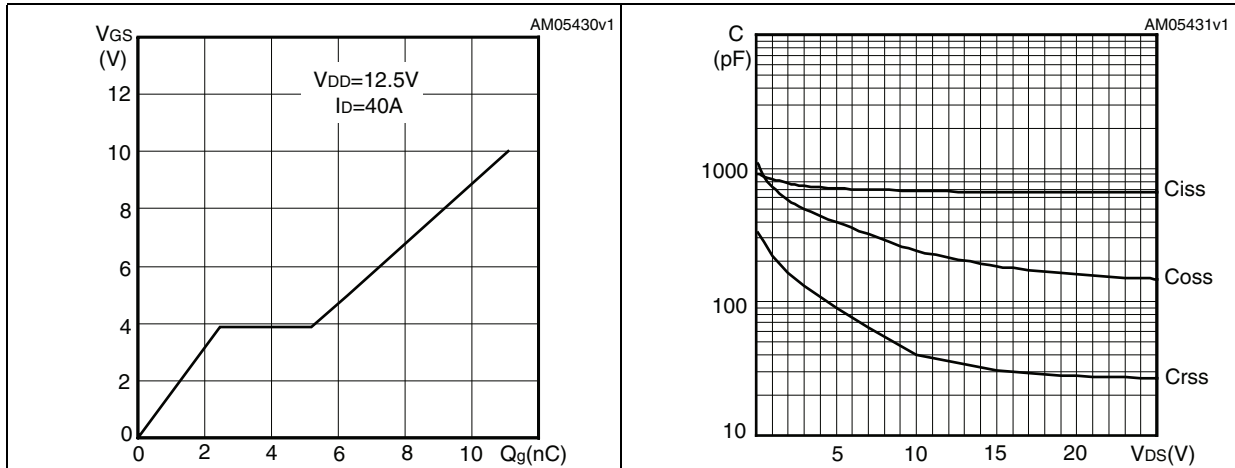


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

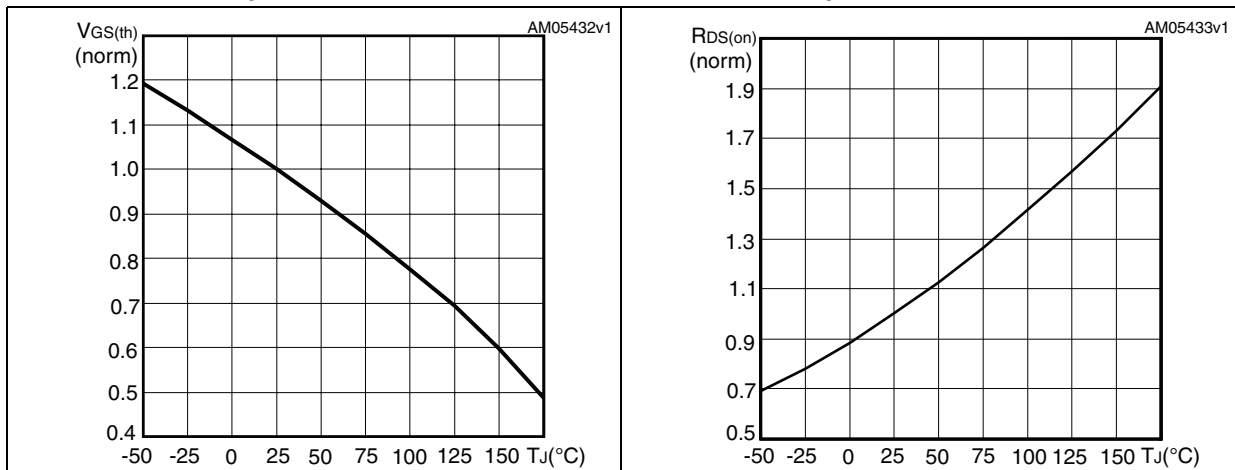
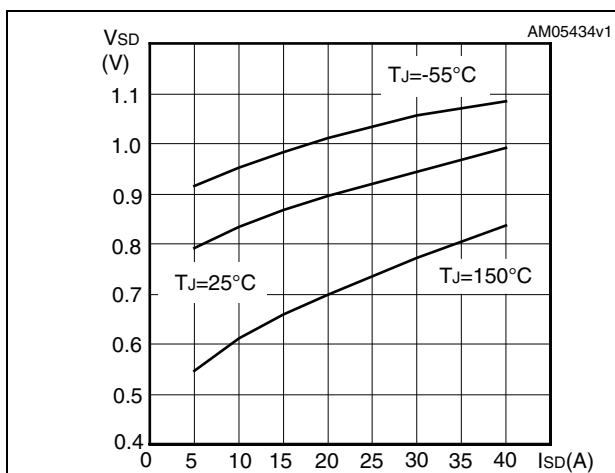
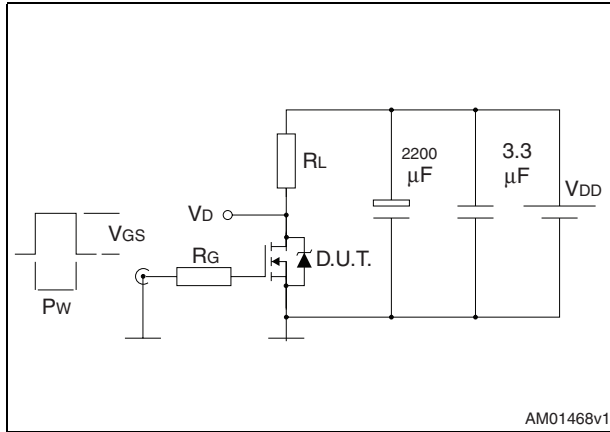


Figure 12. Source-drain diode forward characteristics

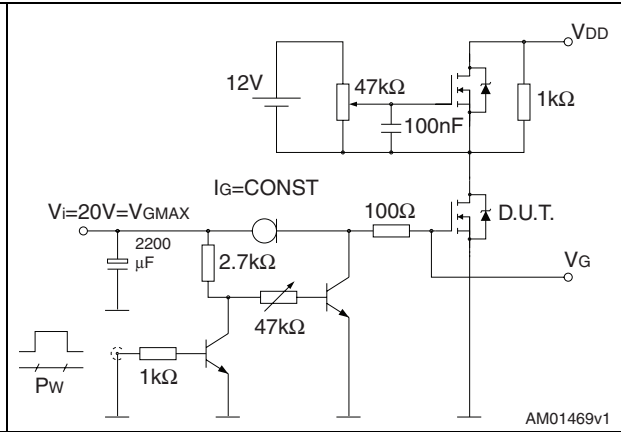


### 3 Test circuits

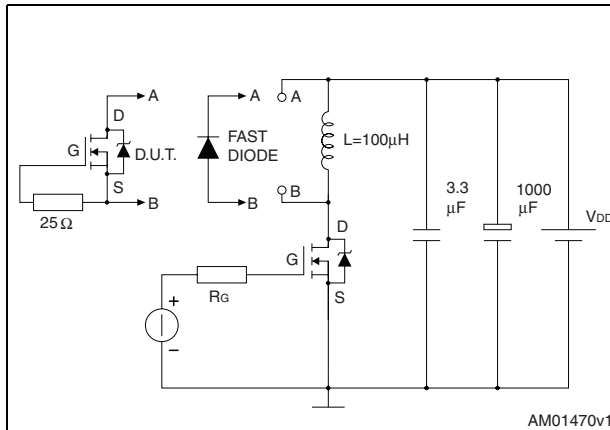
**Figure 13. Switching times test circuit for resistive load**



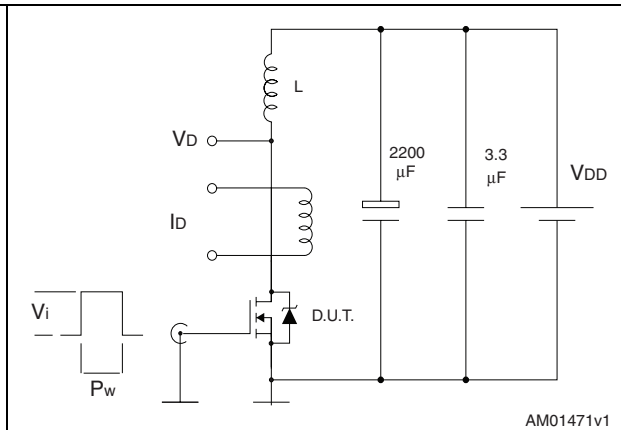
**Figure 14. Gate charge test circuit**



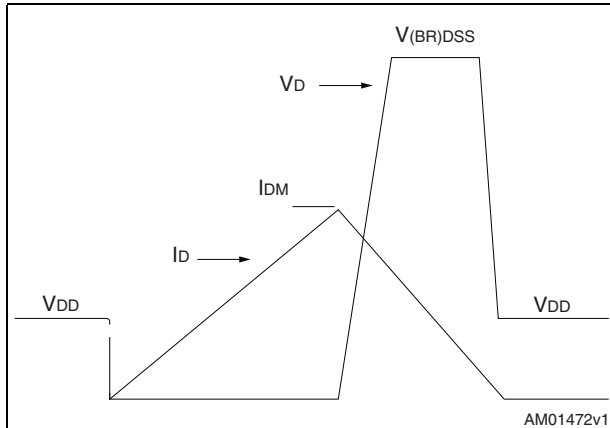
**Figure 15. Test circuit for inductive load switching and diode recovery times**



**Figure 16. Unclamped Inductive load test circuit**



**Figure 17. Unclamped inductive waveform**



**Figure 18. Switching time waveform**

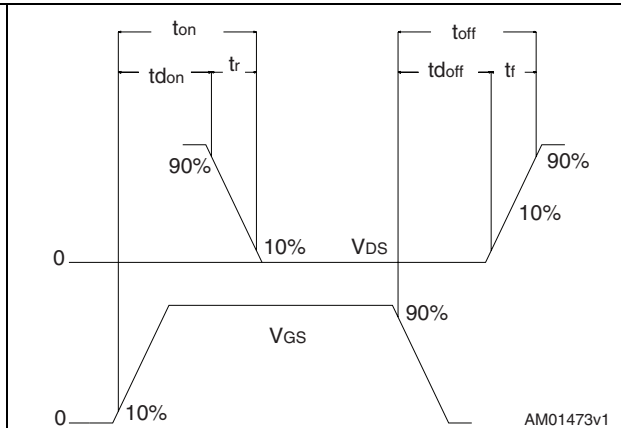
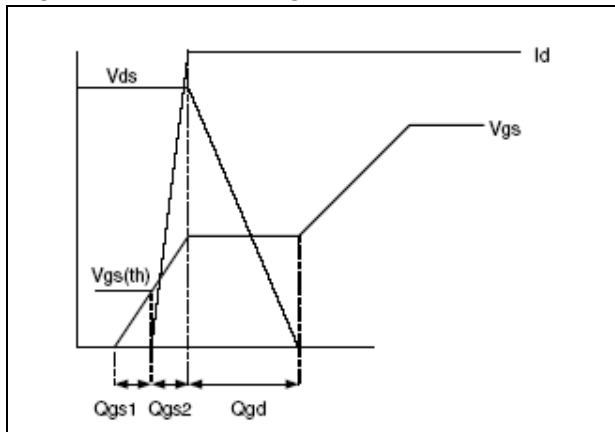




Figure 19. Gate charge waveform

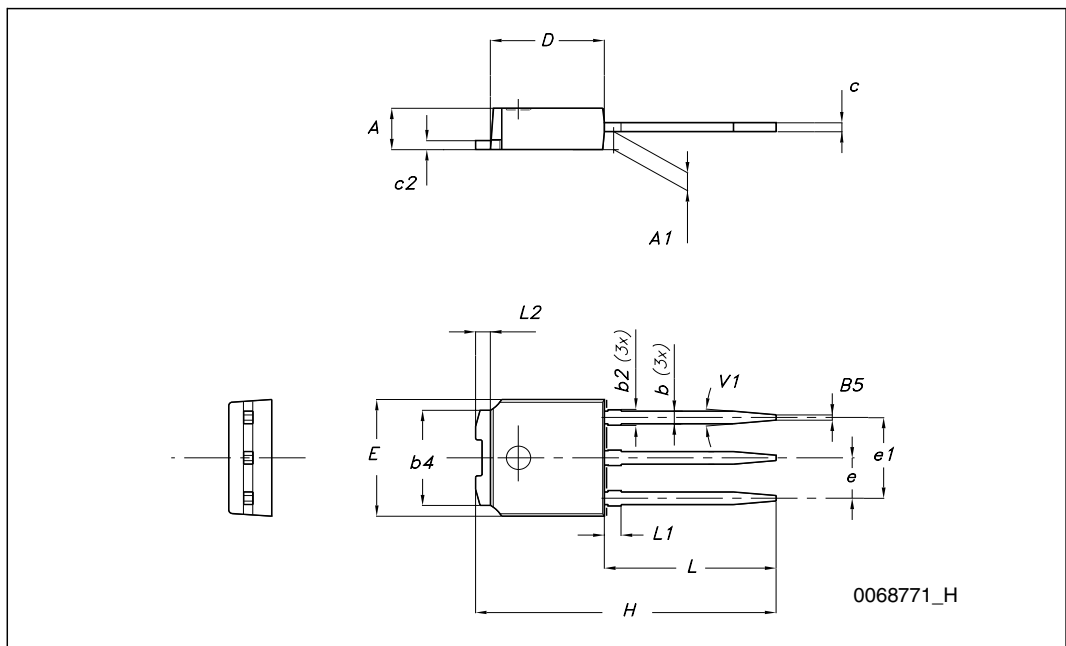


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

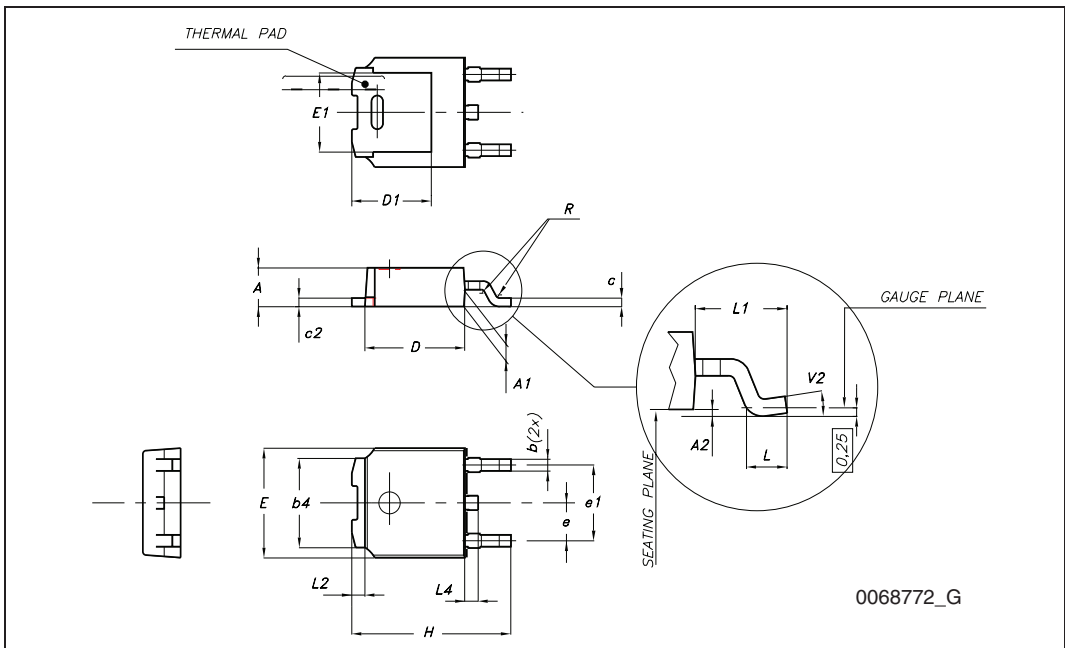
**TO-251 (IPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



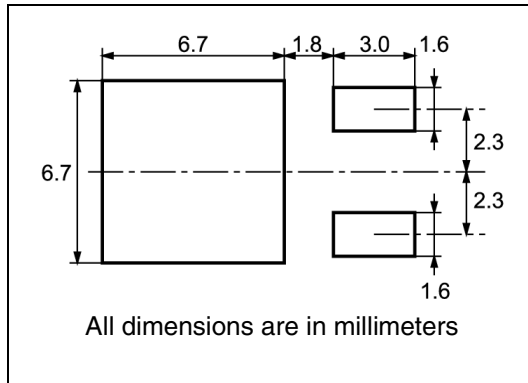
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



# 5 Packaging mechanical data

## DPAK FOOTPRINT



## TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start  
2.5mm min. width

G measured at hub

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

For machine ref. only including draft and radii concentric around B0

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

## 6 Revision history

**Table 8. Document revision history**

Date	Revision	Changes
24-Jul-2008	1	Initial release
23-Sep-2008	2	$V_{GS}$ value has been changed on <a href="#">Table 2</a> and <a href="#">Table 5</a>
10-Sep-2009	3	Document status promoted from preliminary data to datasheet.

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